

Supplementary Information

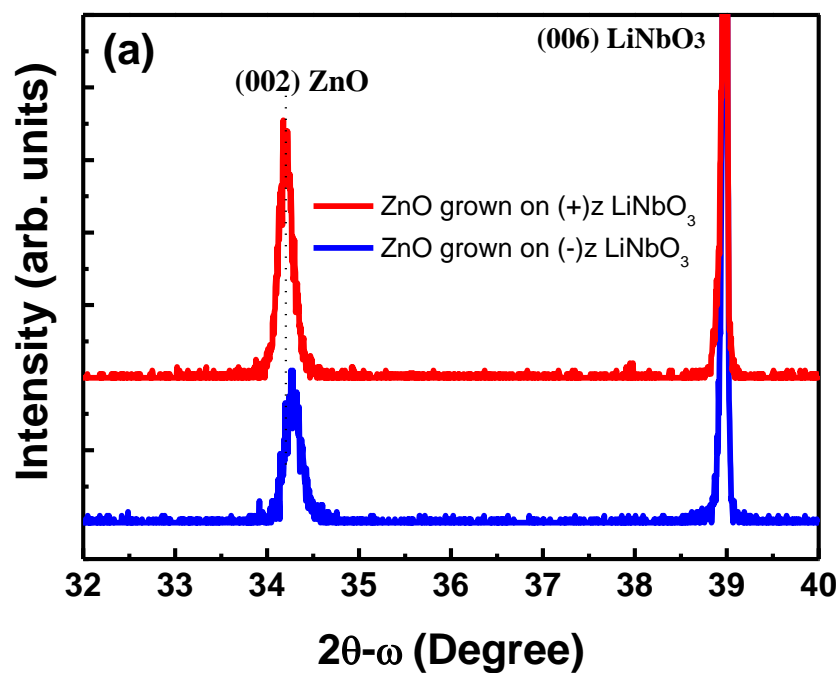
Polarity control of ZnO films grown on ferroelectric (0001) LiNbO₃ substrates without buffer layers by the pulsed-laser deposition

Im Taek Yoon¹, Juwon Lee^{1,*}, Ngoc Cuong Tran² and Woochul Yang^{2,*}

¹ Quantum Functional Semiconductor Research Center (QSRC), Dongguk University, 26 Phildong 3ga, Chung gu, Seoul, 100-715, Republic of Korea

² Department of Physics, Dongguk University, 26 Phildong 3ga, Chung gu, Seoul, 100-715, Republic of Korea

*Corresponding author: E-mail: wyang@dongguk.edu, juji99@dongguk.edu



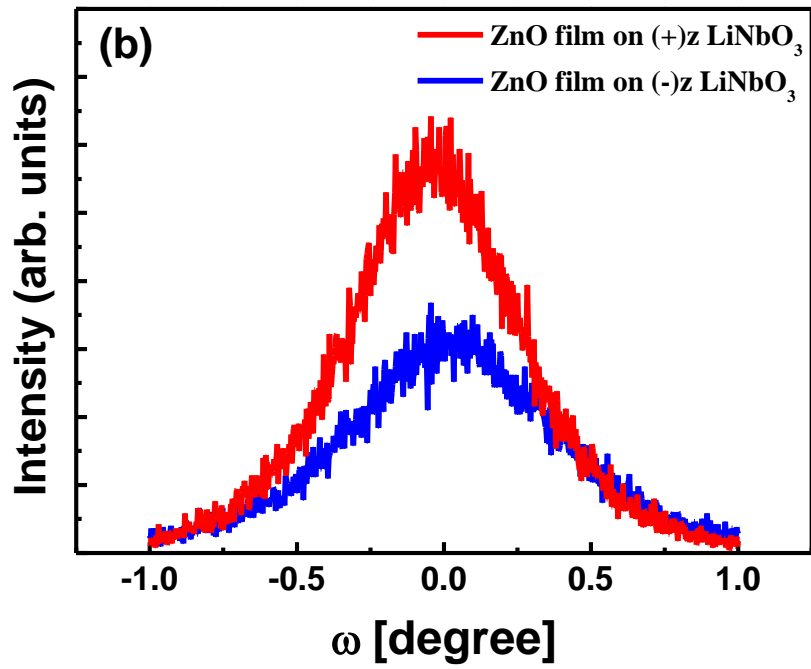


Figure S1 (a) The 2θ - ω scan of the XRD spectra of the ZnO/(+z) LiNbO₃ and ZnO/(-z) LiNbO₃ thin films. (b) The ω -rocking curves of the ZnO/(+z) LiNbO₃ and ZnO/(-z) LiNbO₃ thin films.

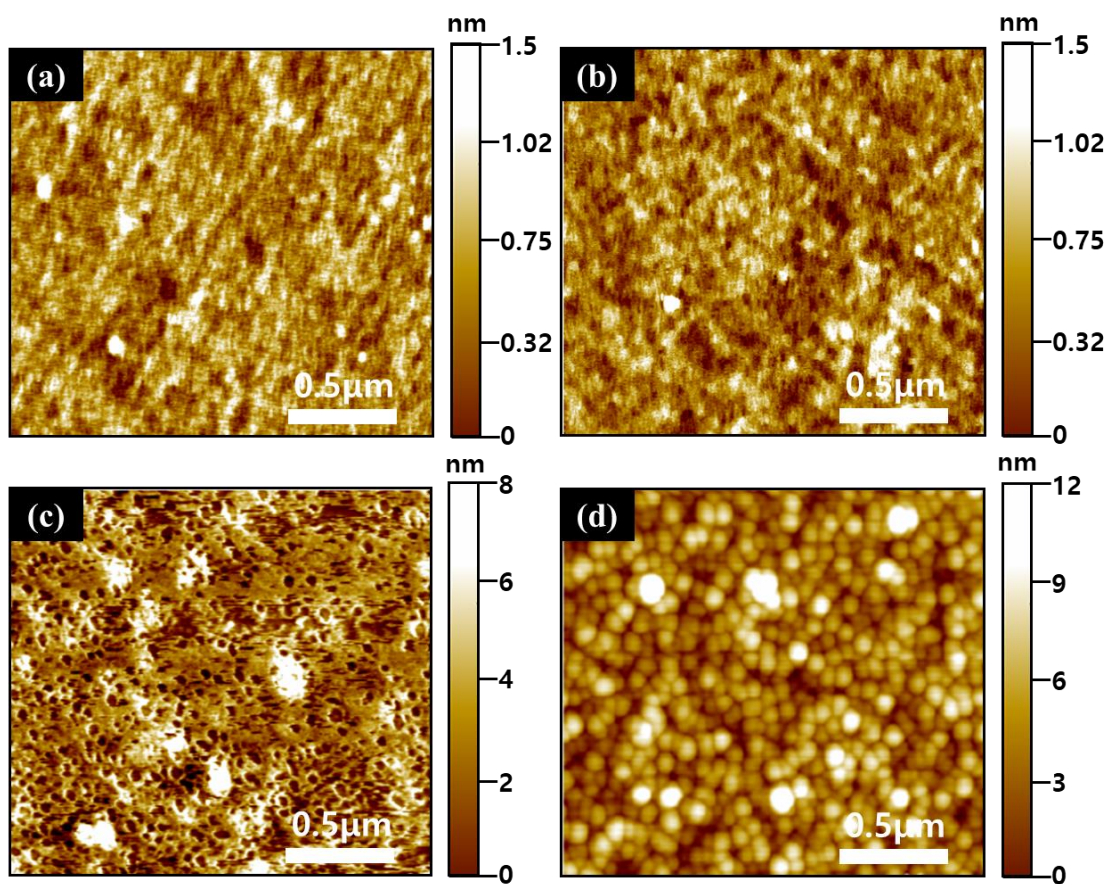


Figure S2 AFM images of the Zn-polar and the O-polar in the bulk-ZnO samples. (a) Zn-polar of the ZnO bulk before the etching. (b) O-polar of the ZnO bulk before the etching. (c) Zn-polar of the ZnO bulk after the etching. (d) O-polar of the ZnO bulk after the etching.